



MBR30100CN-ST

SCHOTTKY BARRIER DIODE

APPLICATIONS

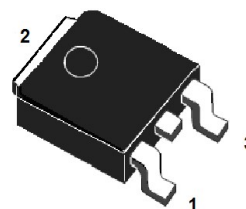
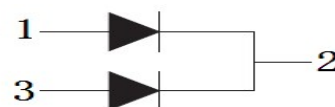
- High frequency switch power supply
- Free wheeling diodes, polarity protection applications

FEATURES

- Common cathode structure
- Low power loss, high efficiency
- High Operating Junction Temperature
- Guard ring for overvoltage protection, High reliability
- RoHS product

MAIN CHARACTERISTICS

$I_{F(AV)}$	30 (2×15) A
V_{RRM}	100 V
T_j	175 °C
$V_{F(max)}$	0.84V (@ $T_j=25^{\circ}C$)



T0-263

ABSOLUTE RATINGS ($T_a=25^{\circ}C$)

Parameter			Symbol	Value	Unit
Repetitive peak reverse voltage			V_{RRM}	100	V
Maximum DC blocking voltage			V_{DC}	100	V
Average forward current	$T_a=25^{\circ}C$	per device	$I_{F(AV)}$	30	A
		per diode		15	
Surge non repetitive forward current		per diode	I_{FSM}	200	A
8.3 ms single half-sine-wave (JEDEC Method)					
Maximum junction temperature			T_j	175	$^{\circ}C$
Storage temperature range			T_{STG}	-40~+150	$^{\circ}C$



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ELECTRICAL CHARACTERISTICS

Parameter	Tests conditions		Value(min)	Value(typ)	Value(max)	Unit
I_R	$T_j = 25^{\circ}\text{C}$	$V_R = V_{RRM}$		0.4	5	μA
V_F	$T_j = 25^{\circ}\text{C}$	$I_F = 15\text{A}$		0.84	0.90	V

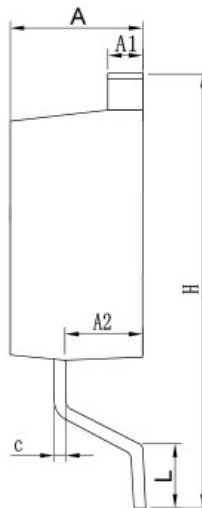
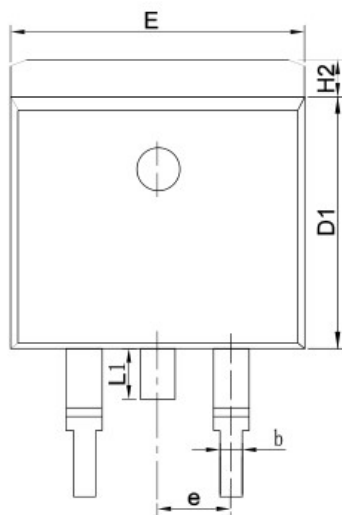


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PACKAGE MECHANICAL DATA

Unit : mm

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SYMBOL	MM	
	MIN	MAX
A	4.30	4.80
A1	1.12	1.42
A2	2.54	2.84
b	0.67	1.00
c	0.29	0.52
D1	8.40	9.00
E	9.80	10.46
e	2.54BSC	
H	14.00	16.00
H2	1.12	1.45
L	1.50	3.10
L1	1.45	1.70